

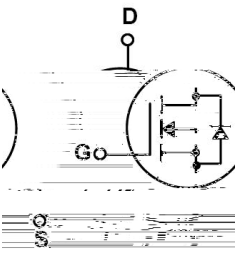
[illegible]



TO-252 N
N-CHANNEL MOSFET in a TO-252 Plastic Package.

$R_{DS(on)}$ C_{rss}
Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

DC/DC
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



PIN1 G PIN 2 D PIN 3 S PIN 4 D

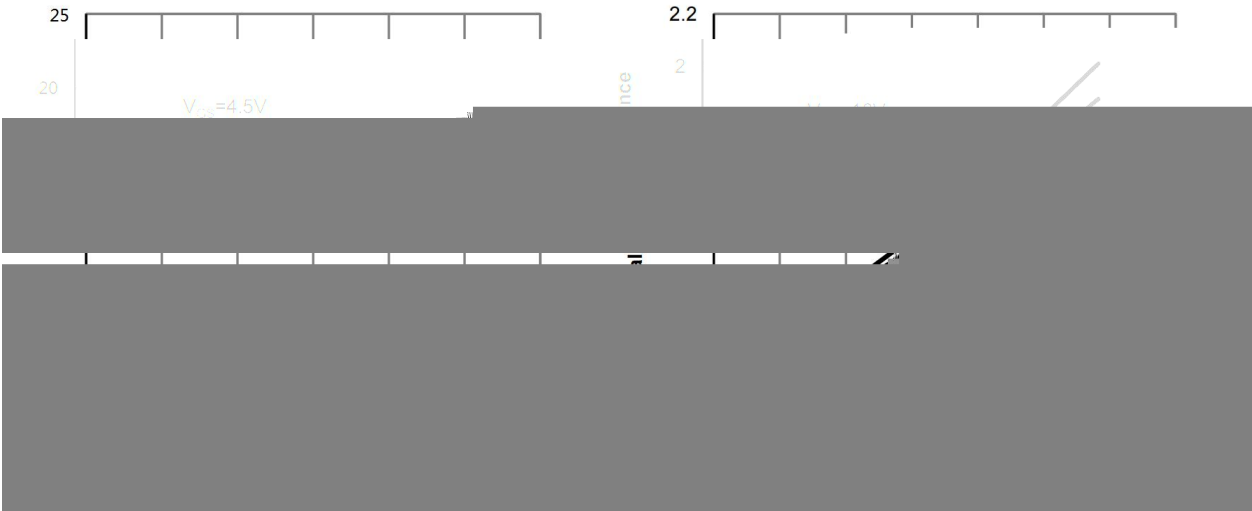
See Marking Instructions.



Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	55	A
Drain Current - Pulsed		I_{DM}	138	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	7.0	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	24.5	mJ
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	73	W
Storage Temperature Range		T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	20	$^\circ\text{C/W}$
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.7	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$	100	108		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}$ $V_{GS}=0\text{V}$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=20\text{V}$ $V_{DS}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu\text{A}$	1.5	1.8	2.5	V

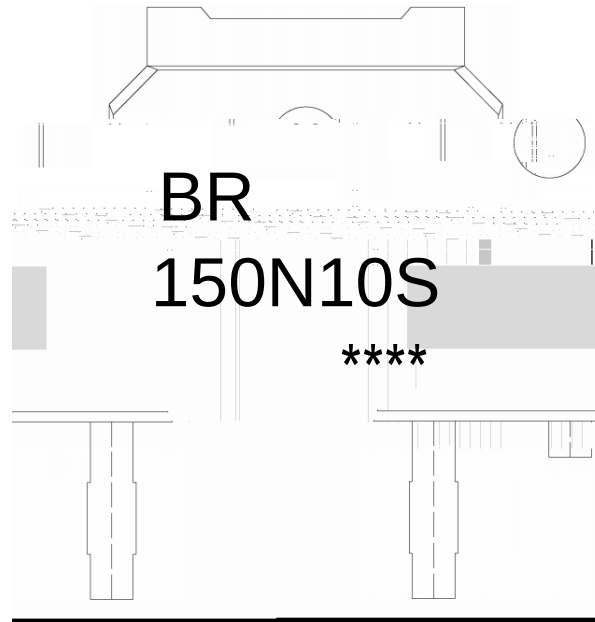
Static Drain-Source
On-





Rev.A Feb.-2022

<http://>



BR

150N10S

Note:

BR: Company Code

150N10S: Product Type Code

****: Lot No. Code, code change with Lot No



				Note:
1	150	180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5		5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10	/sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5℃	Time:10±1 sec
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/ REEL

Package Type	Units	Dimension	(unit mm
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